

In the Claims

Please cancel claims 1-12 and 15, and amend claims 13 and 14 as marked-up on page 4, by deleting the matter shown by strike through and inserting the underlined matter. A clean copy of claims 13 and 14, as amended, is listed below.

13. (Amended) A method of fabricating a semiconductor device comprising a silicon substrate carrying a ground plane, a dielectric layer provided on said ground plane, a signal layer provided on said dielectric layer, a depression formed in said dielectric layer so as to extend down to said substrate through said signal layer and said ground plane, and a semiconductor chip carrying thereon an air bridge structure, said semiconductor chip being flip chip mounted onto said silicon substrate, said method comprising the steps of:

forming said depression in said silicon substrate by an etching process; and

mounting said semiconductor chip on said silicon substrate such that said air bridge structure is accommodated into said depression.

14. (Amended) A method as claimed in claim 13, wherein said etching step includes a wet etching process applied to said silicon substrate.